



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

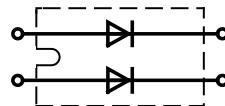
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

# Fast Recovery Epitaxial Diode (FRED)

$I_{FAVM} = 2 \times 52 A$   
 $V_{RRM} = 1200 V$   
 $t_{rr} = 40 ns$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
1200	1200	DSEI 2x 61-12B



miniBLOC, SOT-227 B



E72873

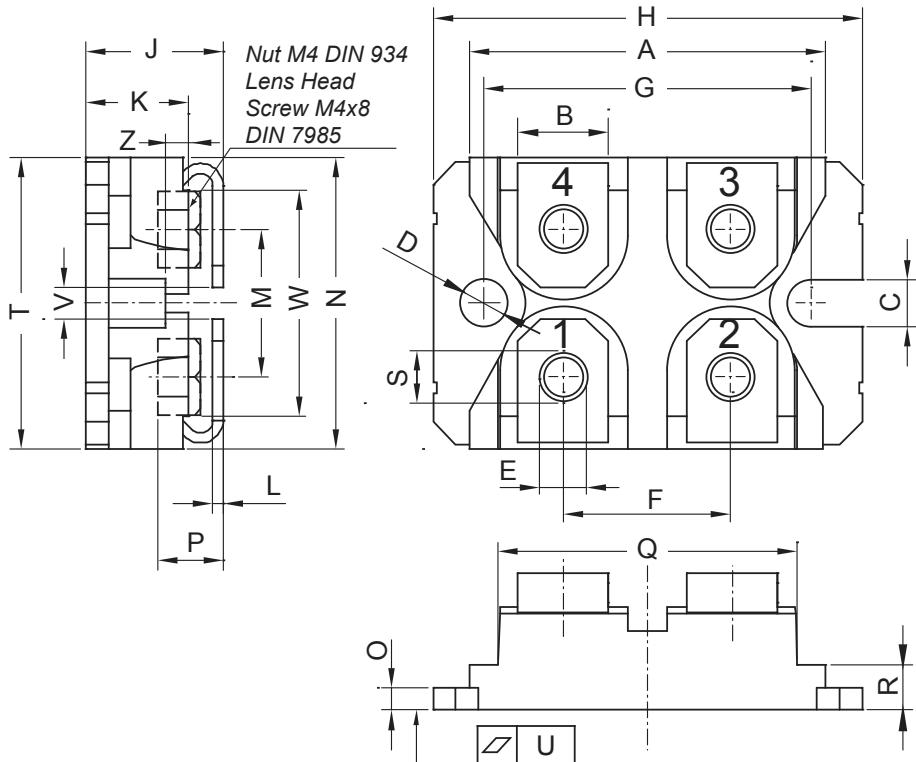
Symbol	Conditions	Maximum Ratings (per diode)		
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	100	A	
$I_{FAVM}$ ①	$T_c = 50^\circ C$ ; rectangular, $d = 0.5$	52	A	
$I_{FRM}$	$t_p < 10 \mu s$ ; rep. rating, pulse width limited by $T_{VJM}$	700	A	
$I_{FSM}$	$T_{VJ} = 45^\circ C$ ; $t = 10 ms$ (50 Hz), sine	450	A	
	$t = 8.3 ms$ (60 Hz), sine	500	A	
	$T_{VJ} = 150^\circ C$ ; $t = 10 ms$ (50 Hz), sine	400	A	
	$t = 8.3 ms$ (60 Hz), sine	440	A	
$I^2t$	$T_{VJ} = 45^\circ C$ $t = 10 ms$ (50 Hz), sine	1000	$A^2s$	
	$t = 8.3 ms$ (60 Hz), sine	1050	$A^2s$	
	$T_{VJ} = 150^\circ C$ ; $t = 10 ms$ (50 Hz), sine	800	$A^2s$	
	$t = 8.3 ms$ (60 Hz), sine	810	$A^2s$	
$T_{VJ}$		-40...+150	$^\circ C$	
$T_{VJM}$		150	$^\circ C$	
$T_{stg}$		-40...+150	$^\circ C$	
$P_{tot}$	$T_c = 25^\circ C$	180	W	
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	2500	V~	
$M_d$	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in Nm/lb.in	
Weight		30	g	
Symbol	Conditions	Characteristic Values (per diode)		
		typ.	max.	
$I_R$	$T_{VJ} = 25^\circ C$ $V_R = V_{RRM}$	2.2	mA	
	$T_{VJ} = 25^\circ C$ $V_R = 0.8 \cdot V_{RRM}$	0.5	mA	
	$T_{VJ} = 125^\circ C$ $V_R = 0.8 \cdot V_{RRM}$	14	mA	
$V_F$	$I_F = 60 A$ ; $T_{VJ} = 150^\circ C$	2.15	V	
	$T_{VJ} = 25^\circ C$	2.50	V	
$V_{TO}$	For power-loss calculations only	1.65	V	
$r_T$	$T_{VJ} = T_{VJM}$	8.3	$m\Omega$	
$R_{thJC}$		0.7	K/W	
$R_{thCK}$		0.05	K/W	
$t_{rr}$	$I_F = 1 A$ ; $-di/dt = 200 A/\mu s$ ; $V_R = 30 V$ ; $T_{VJ} = 25^\circ C$	40	60	ns
$I_{RM}$	$V_R = 540 V$ ; $I_F = 60 A$ ; $-di_F/dt = 480 A/\mu s$ $L \leq 0.05 \mu H$ ; $T_{VJ} = 100^\circ C$	32	36	A

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$   
Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions.

20170315a

## miniBLOC, SOT-227 B



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

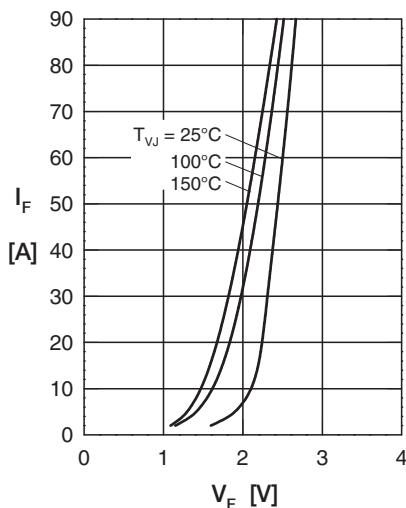


Fig. 1 Forward current  
vs. voltage drop

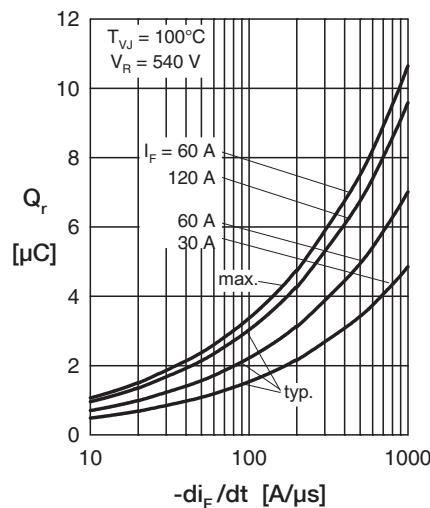


Fig. 2 Recovery charge  
versus  $-\frac{dI_F}{dt}$

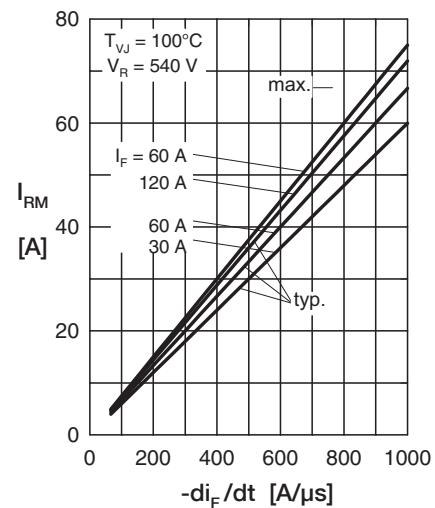


Fig. 3 Peak reverse current  
versus  $-\frac{dI_F}{dt}$

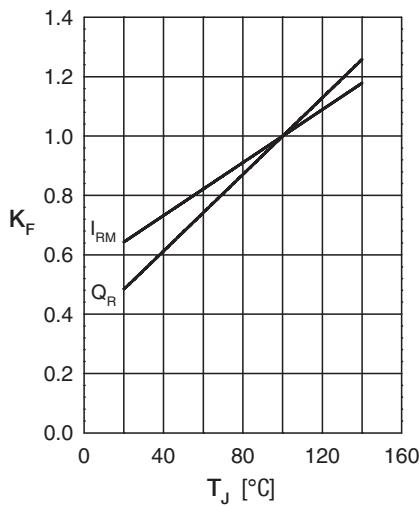


Fig. 4 Dyn. parameters vs.  
junction temperature

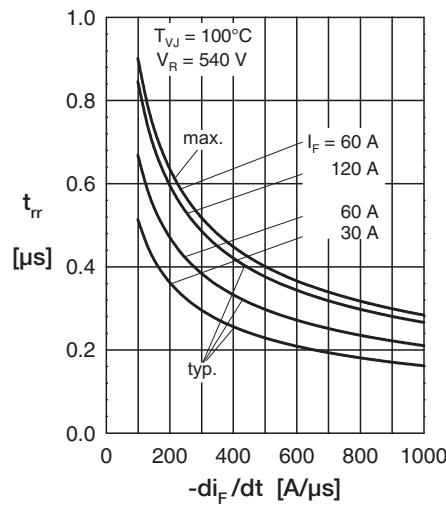


Fig. 5 Recovery time  
versus  $-\frac{dI_F}{dt}$

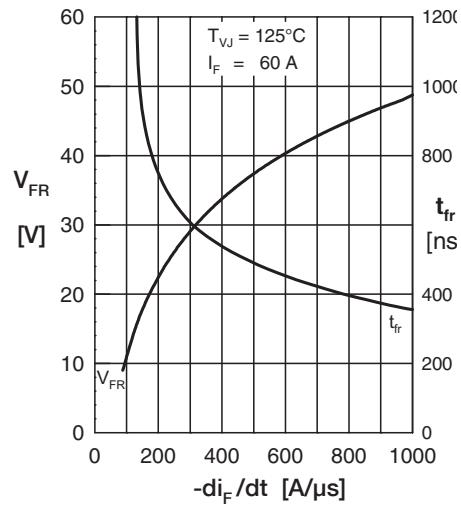


Fig. 6 Peak forward voltage  
versus  $-\frac{dI_F}{dt}$

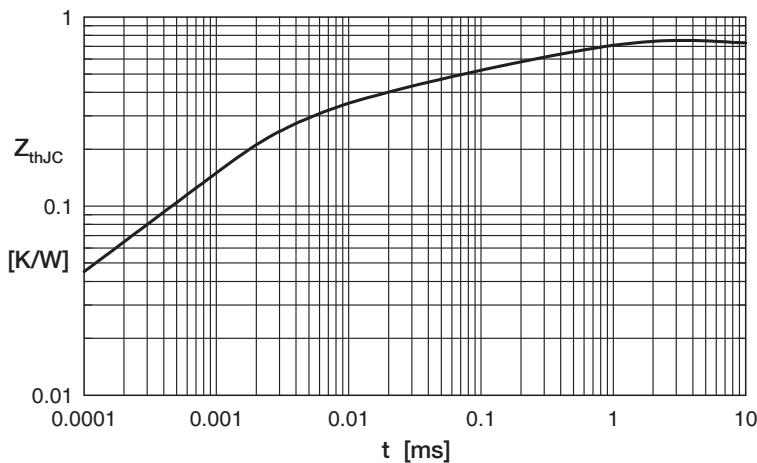


Fig. 7 Transient thermal impedance junction to case